L Number	Hits	Search Text	DB	Time stamp
1	7756671	via or opening or trench or v-trench or groove or v-groove or contact or	USPAT;	2003/09/29 09:08
		recess or cavity or cavities or hole or damascene	US-PGPUB;	
			EPO; JPO;	ļ
			DERWENT;	
	200		IBM_TDB	
2	289	(via or opening or trench or v-trench or groove or v-groove or contact or	USPAT;	2003/09/29 09:10
		recess or cavity or cavities or hole or damascene) and 216/37	US-PGPUB;	
_			ЕРО; ЈРО;	ļ
			DERWENT;	
			IBM_TDB	
3	12	((via or opening or trench or v-trench or groove or v-groove or contact or recess or cavity or cavities or hole or damascene) and 216/37) and 438/734	USPAT;	2003/09/29 10:05
			US-PGPUB;	
ļ			EPO; JPO;	
			DERWENT;	
_			IBM_TDB	
5	0	438/638.ccls. with (oxygen or o2 or osub2 or "o.sub.2")	USPAT;	2003/09/29 10:06
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
5	1646	438/637.ccls.	USPAT;	2003/09/29 10:06
			US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
7	. 0	438/637.ccls. with (oxygen or o2 or osub2 or "o.sub.2")	USPAT;	2003/09/29 10:06
			US-PGPUB;	
į			EPO; JPO;	
			DERWENT,	-
4			IBM_TDB	į
	543	438/638.ccls.	USPAT;	2003/09/29 11:27
			US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
	21	photoresist with low-k with (spin-on polymer)	USPAT;	2003/09/29 11:39
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	15	photoresist with (spin-on adj polymer)	USPAT;	2003/09/29 11:42
10			US-PGPUB;	
			ЕРО; ЈРО;	
			DERWENT,	
	G.12		IBM_TDB	
0	742	photoresist with (low-k or (low adj dielectric) or silk or flare or (organic	USPAT;	2003/09/29 12:51
		adj (ild dielectric interlayer)))	US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
	<b>7</b> 0		IBM_TDB	
11	79	(photoresist with (low-k or (low adj dielectric) or silk or flare or	USPAT;	2003/09/29 11:53
		(organic adj (ild dielectric interlayer)) )) with (oxygen or o2 or	US-PGPUB;	
		"o.sub.2")	ЕРО; ЛРО;	
			DERWENT;	
12	1241	/ // m	IBM_TDB	
12	1341	(pattern\$ near4 photoresist) with (oxygen or o2 or "o.sub.2")	USPAT;	2003/09/29 11:53
			US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	

13	1786	((remov\$4 near1 portion) or pattern\$4) with photoresist with (oxygen or	USPAT;	2003/09/29 11:55
j		o2 or "o.sub.2")	US-PGPUB;	
			ЕРО; ЈРО;	
			DERWENT;	
ı			IBM_TDB	
14	70	(remov\$4 near1 portion) with photoresist with (oxygen or o2 or	USPAT;	2003/09/29 11:56
		"o.sub.2")	US-PGPUB;	
			ЕРО; ЈРО;	
			DERWENT;	
			IBM_TDB	
15	109	photoresist with (low-k or (low adj dielectric) or silk or flare ) with	USPAT,	2003/09/29 12:51
	Ì	organic	US-PGPUB,	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
16	19	(low-k or (low adj dielectric) or silk or flare ) adj mask\$4	USPĀT;	2003/09/29 12:52
-			US-PGPUB,	
			EPO, JPO,	
			DERWENT;	
			IBM_TDB	
17	199	(low-k or (low adj dielectric)) near3 mask\$4	USPAT;	2003/09/29 12:52
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
18	48	((low-k or (low adj dielectric)) near3 mask\$4) with photoresist	USPAT;	2003/09/29 12:55
			US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
	Į		IBM_TDB	
19	151	((low-k or (low adj dielectric)) near3 mask\$4) not (((low-k or (low adj	USPAT;	2003/09/29 12:55
	1	dielectric)) near3 mask\$4) with photoresist)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	